

650V Silicon Carbide Schottky Diode

DESCRIPTION:

- High surge current capability
- No reverse recover
- · High Speed Switching
- · Positive temperature Coefficient
- · Easy to paralleling
- · RoHS Compliant

- · Switch mode power supplies
- · Solar inverters
- · Data Center
- · Power factor correction

V_{RRM}	650V		
I _F	20A (TC=153°C)		
Q_{C}	62nC		



TO-263 (D2-PAK)

MAXIMUM RATINGS (at T_C = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	650	V
Continuous Forward Current	Tc=25℃ Tc=135℃ Tc=153℃	I _F	61 28 20	А
Non-Repetitive Forward Surge Current	Tc=25°C , t_P =10ms, Half sine pulse Tc=110°C , t_P =10ms, Half sine pulse	I _{FSM}	142 135	А
Repetitive Peak Forward Surge Current	Tc=25°C , t _P =10ms, Half sine pulse	I _{FRM}	130	А
i ² t value	Tc=25 $^{\circ}$ C , t _P =10ms Tc=110 $^{\circ}$ C , t _P =10ms	∫ i ² dt	100 91	A ² S
Power dissipation	Tc=25℃ Tc=110℃ Tc=150℃	P _{tot}	250 108 41	W
Operation Junction temperature		Tj	-55~+175	$^{\circ}\!\mathbb{C}$
Storage temperature		T _{STG}	-55~+175	$^{\circ}\!\mathbb{C}$

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Typical	Unit
Thermal resistance, junction - case		$R_{\text{th(j-C)}}$	0.60	%C/W

ELECTRICAL CHARATERISTICS (at $T_C = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V _{DC}	650			V
Forward Voltage IF = 10A IF = 20A, Tc =25°C IF = 20A, Tc =175°C	V _F		1.16 1.35 1.70	1.6	V
Reverse Current $VR = 650V$, $Tc = 25^{\circ}C$ $VR = 650V$, $Tc = 175^{\circ}C$	I _R		6 15	100	uA
Total Capacitive Charge VR = 400V	Q _C		62		nC
Total capacitance VR = 1V, f =1MHz VR = 200V, f =1MHz VR = 400V, f =1MHz	С		906 122 118		pF
Capacitance Stored Energy VR = 400 V	Ec		10		uJ

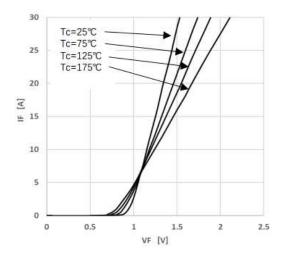


Figure 1. Forward characteristics

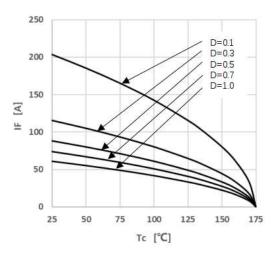


Figure 3. Peak Forward Current Derating

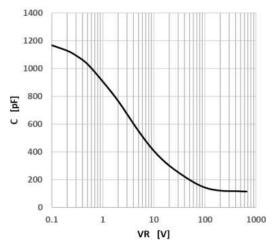


Figure 5. Capacitance vs. Reverse Voltage

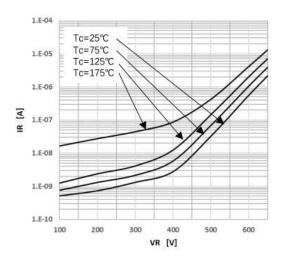


Figure 2. Reverse characteristics

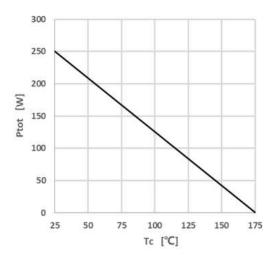


Figure 4. Power Dissipation

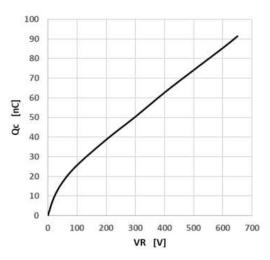


Figure 6. Capacitance Charge vs. Reverse Voltage

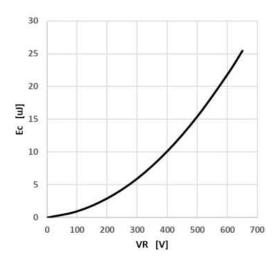


Figure 7. Capacitance Stored Energy

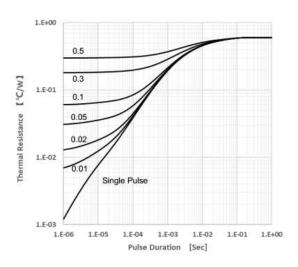
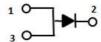
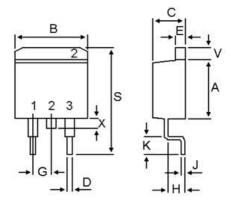


Figure 8. Transient Thermal Impedance

· Circuit diagram



• TO-263 Package outlines : Dimensions in (mm)



	MILLIMETERS		
DIM	MILLIMETERS		
DIIVI	MIN	MAX	
Α	8.30	9.20	
В	9.80	10.40	
C	4.30	4.80	
D	0.65	0.95	
Ш	1.17	1.43	
G	2.39	2.69	
Ι	2.68	3.32	
J	0.35	0.65	
K	2.29	2.90	
S	14.60	15.88	
V	1.10	1.50	
Χ		2.00	



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